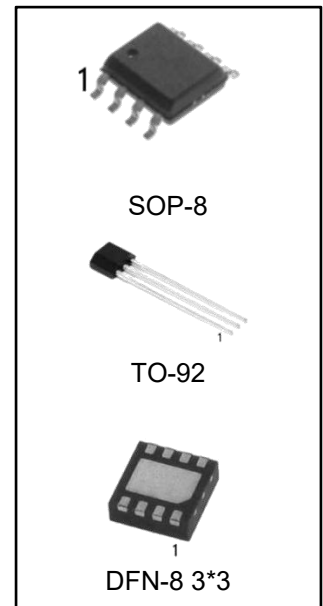


## Description

The LM236 and LM336 are precision 2.5V regulator diodes. These voltage reference monolithic ICs operate like 2.5V zener diodes with a low temperature coefficient and a dynamic impedance of  $0.2\Omega$ . A third pin enables adjusting the reference voltage and the temperature coefficient.

## Features

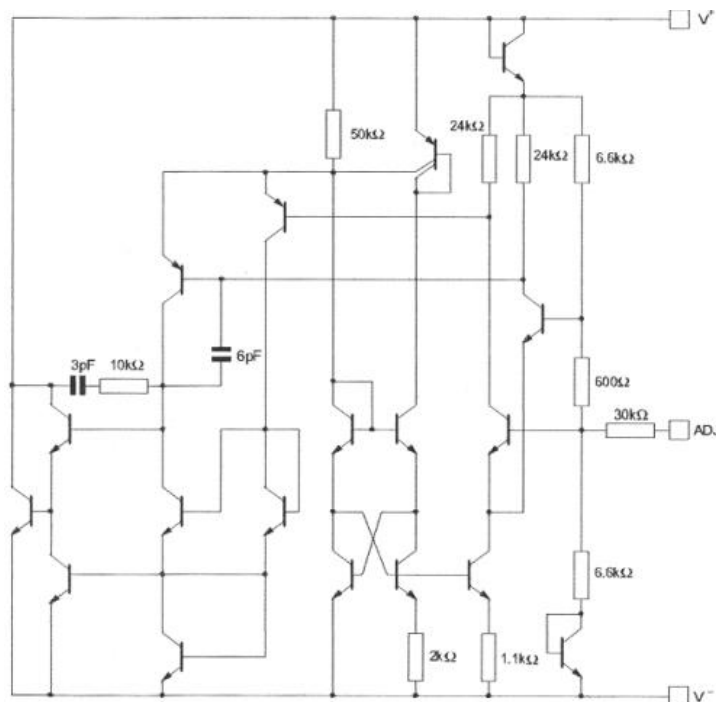
- Low temperature coefficient
- Wide operating current of  $400\mu\text{A}$  to  $10\text{ mA}$
- $0.2\Omega$  dynamic impedance
- $\pm 1\%$  initial tolerance available
- Guaranteed temperature stability
- Fast turn-on



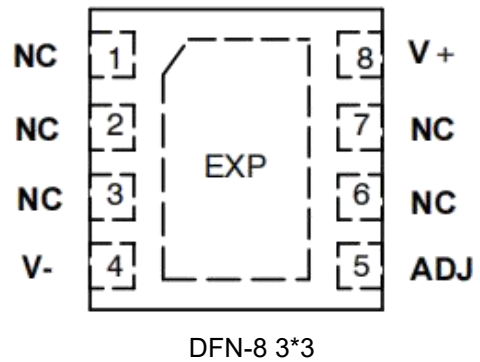
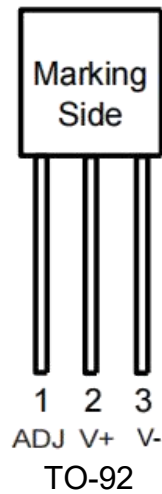
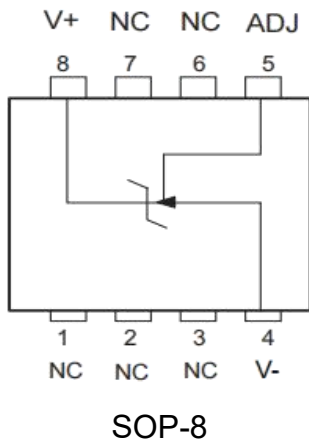
## Ordering Information

DEVICE	Package Type	MARKING	Packing	Packing Qty
LM236M-2.5/TR	SOP-8	236-2.5	Reel	2500pcs/reel
LM336M-2.5/TR	SOP-8	336-2.5	Reel	2500pcs/reel
LM236Z-2.5	TO-92	LM236-2.5	Tape	1000pcs/box
LM336Z-2.5	TO-92	LM336-2.5	Tape	1000pcs/box
LM236DQ-2.5/TR	DFN-8 3*3	236-2.5	Reel	2500pcs/reel
LM336DQ-2.5/TR	DFN-8 3*3	336-2.5	Reel	2500pcs/reel

## Schematic Diagram



## Pin Connections



## Absolute Maximum Ratings

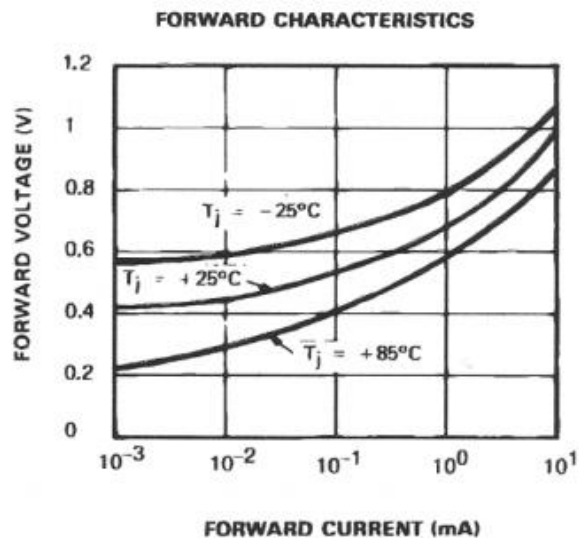
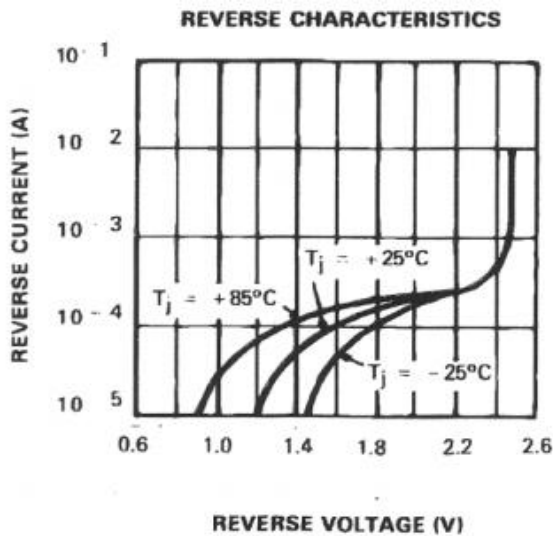
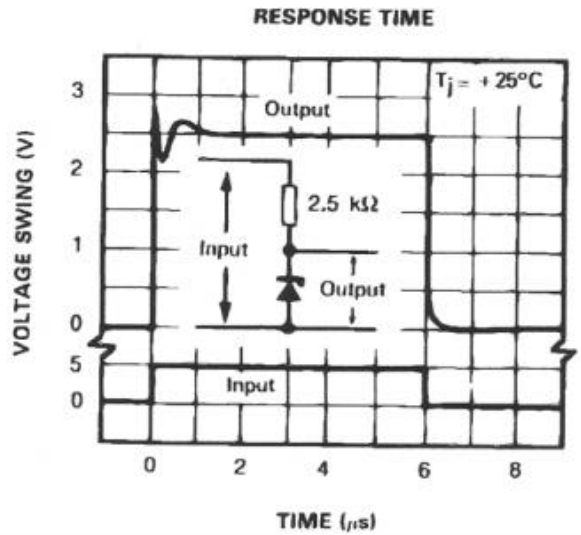
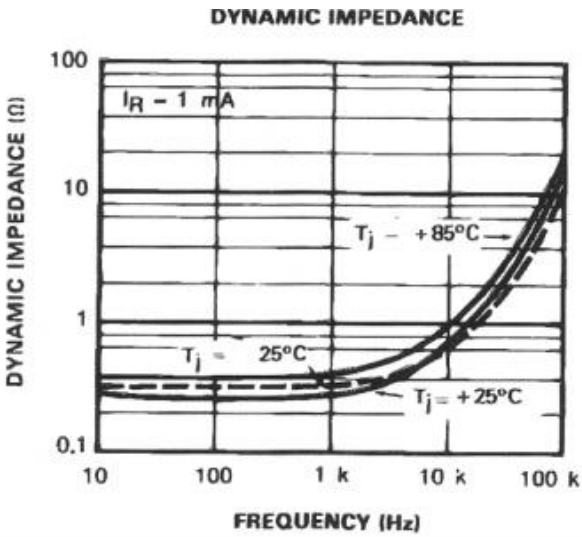
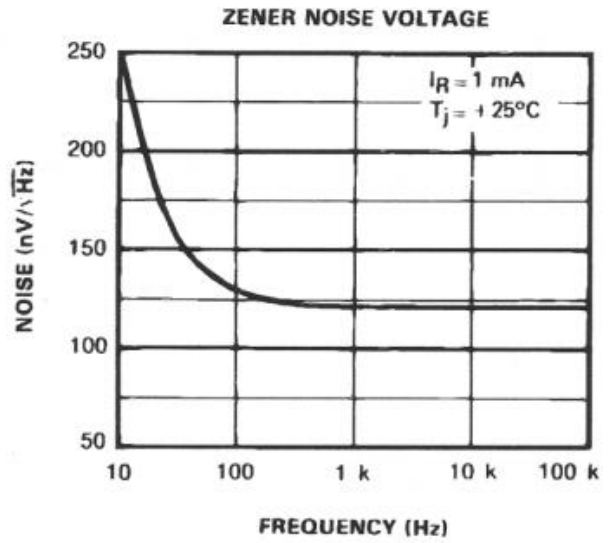
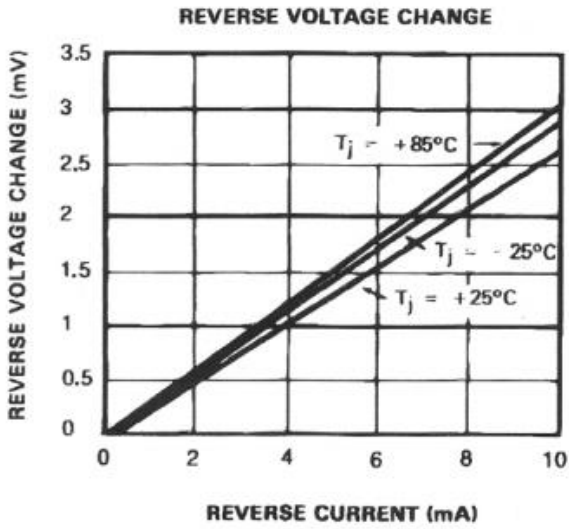
Symbol	Parameter	LM336	Unit
I <sub>RF</sub>	Current Reverse Forward	15	mA
		10	
T <sub>oper</sub>	Operating Free-air Temperature Range	LM336-2.5: 0 to +70	°C
		LM236-2.5: -40 to +85	°C
T <sub>Stg</sub>	Storage Temperature Range	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (Soldering, 10 seconds)	245	°C

**Note:** Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured.

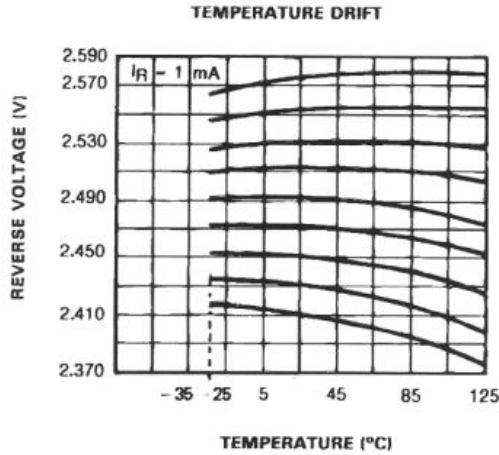
## Electrical Characteristics

Symbol	Parameter	LM236/LM336			Unit
		Min.	Typ.	Max.	
V <sub>R</sub>	Reference Breakdown Voltage T <sub>amb</sub> = +25°C, I <sub>R</sub> = 1mA LM336	2.44	2.49	2.54	V
ΔV <sub>R</sub>	Reverse Breakdown Voltage Change with Current 400μA ≤ I <sub>R</sub> ≤ 10mA T <sub>amb</sub> = +25°C T <sub>min.</sub> ≤ T <sub>amb</sub> ≤ T <sub>max.</sub>	-	2.6 3	10 12	mV
Z <sub>D</sub>	Reverse Dynamic Impedance (I <sub>R</sub> = 1mA) T <sub>amb</sub> = +25°C T <sub>min.</sub> ≤ T <sub>amb</sub> ≤ T <sub>max.</sub>	-	0.2 0.4	1 1.4	Ω
KVT	Temperature Stability (V <sub>R</sub> = 2.49V, I <sub>R</sub> = 1mA)	-	1.8	6	mV
KVH	Long Term Stability (T <sub>amb</sub> = +25°C ±0.1°C, I <sub>R</sub> = 1mA)	-	20	-	ppm

Typical Performance Characteristics



**Typical Performance Characteristics** (Continued)



**Application Hints**

The LM336 voltage references are easier to use than zener diodes. Their low impedance and wide current range facilitate biasing in any circuits. Besides, the breakdown voltage or the temperature coefficient can be adjusted so as to optimize the performance of the circuit.

Figure 1 represents a LM336 with a 10kΩ potentiometer to adjust the reverse breakdown voltage which can be adjusted without altering the temperature coefficient of the circuit. The adjustment range is generally sufficient to adjust the initial tolerance of the circuit and the inaccuracy of the amplifier circuit.

To obtain a lower temperature coefficient two diodes can be connected in series as indicated in Figure 2. When the circuit is adjusted to 2.49V the temperature coefficient is minimized. For a correct temperature coefficient, the diodes should be at the same ambient temperature as the LM336. The value of R1 is not critical (2-20kΩ).

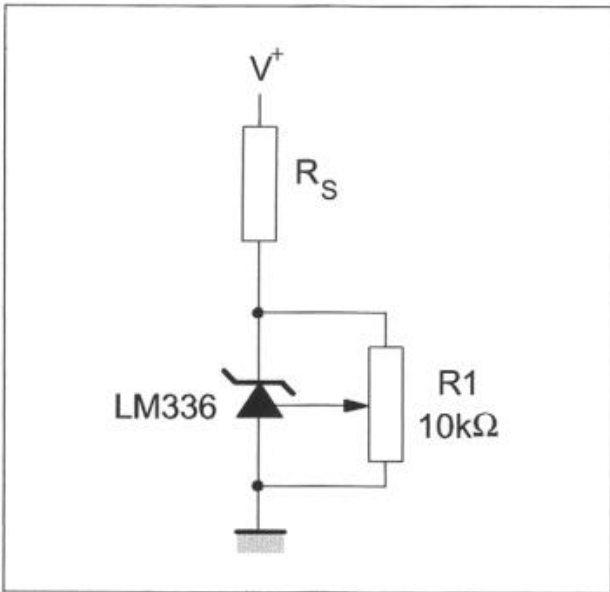


FIGURE1.LM336 with Pot for Adjustment of Breakdown Voltage

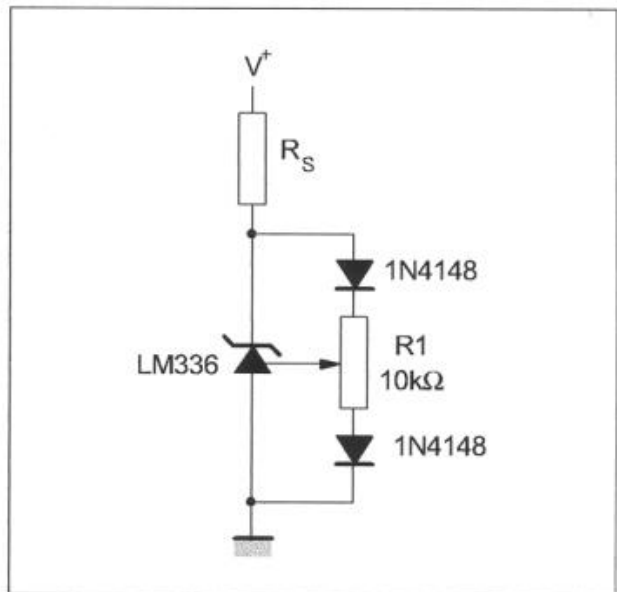


FIGURE 2. Temperature Coefficient Adjustment



Figure 7 :Linear Ohmmeter

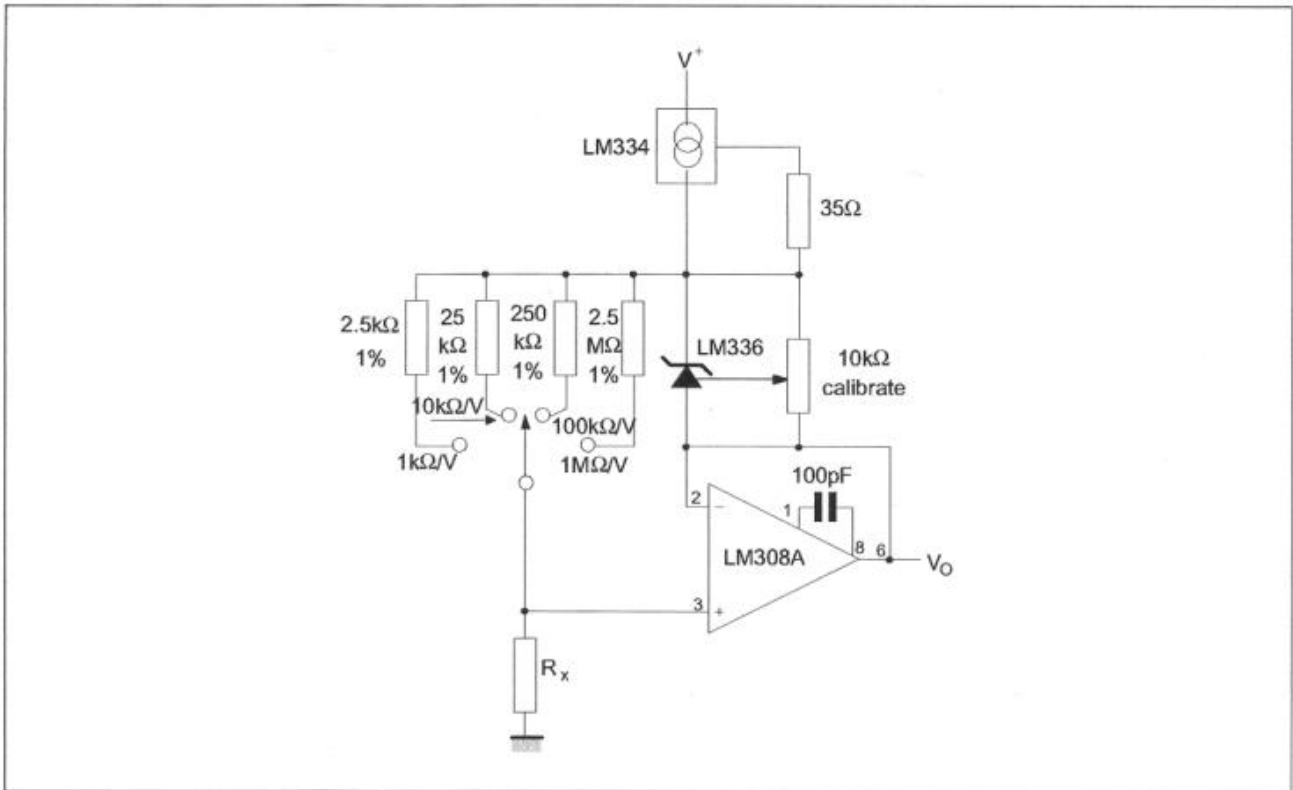


Figure 8 :Bipolar Output Reference

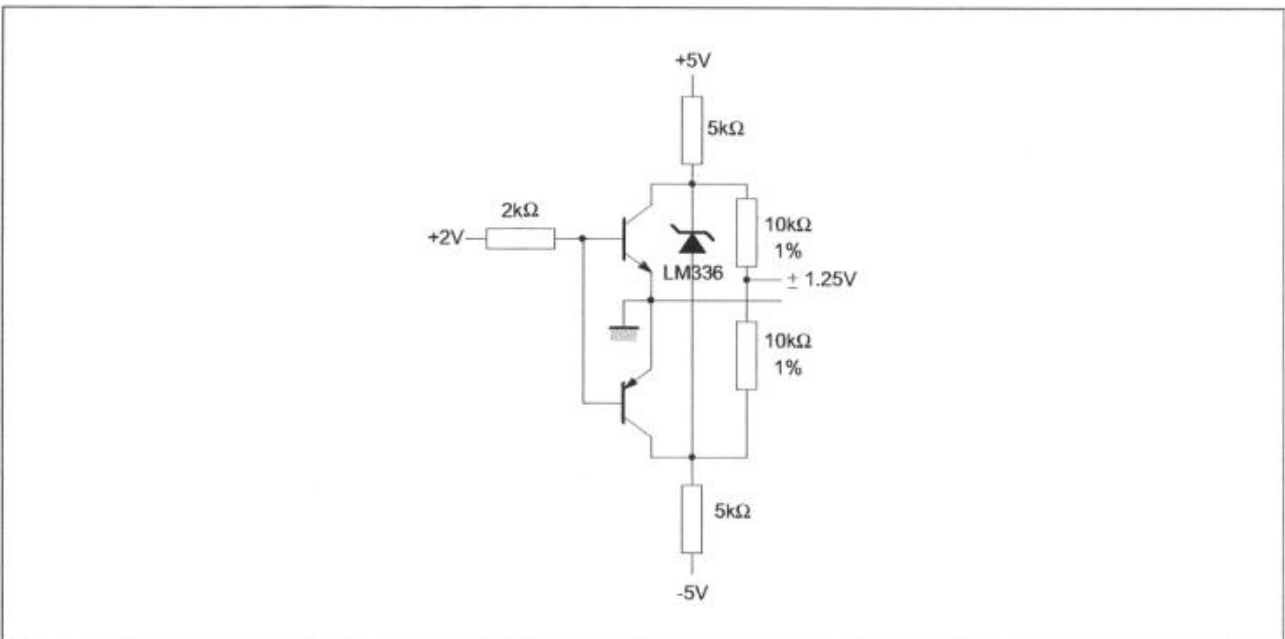


Figure 9 : 5V Buffered Reference

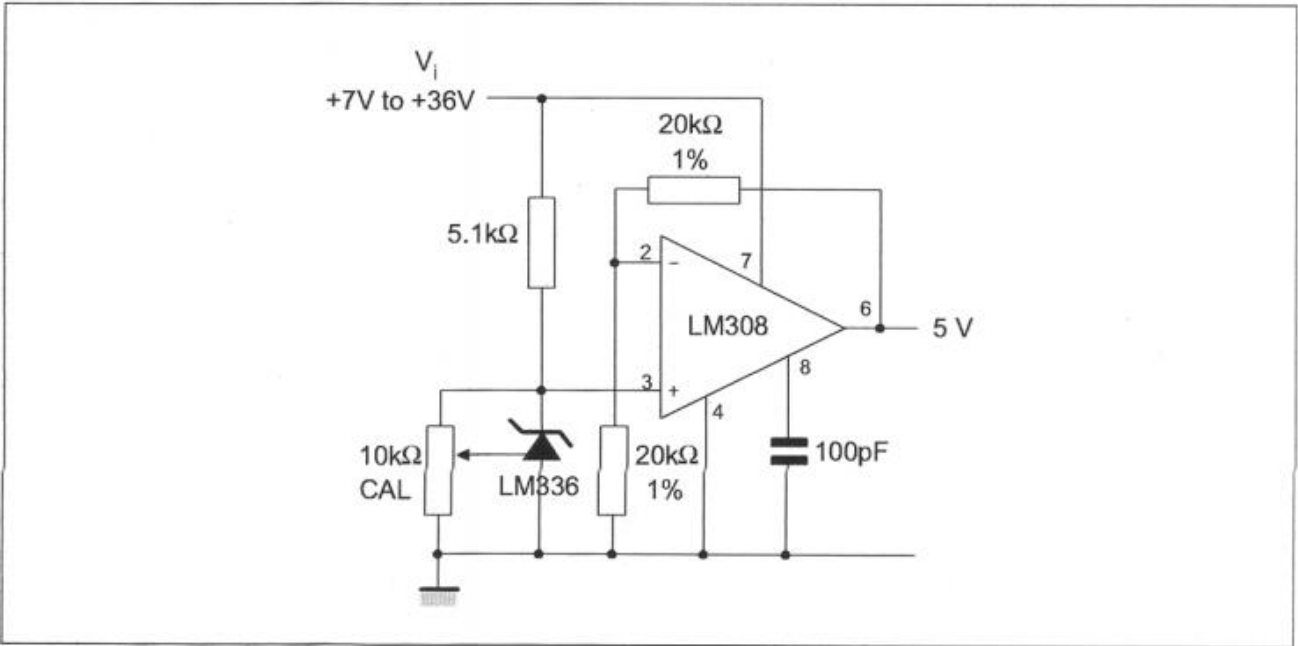
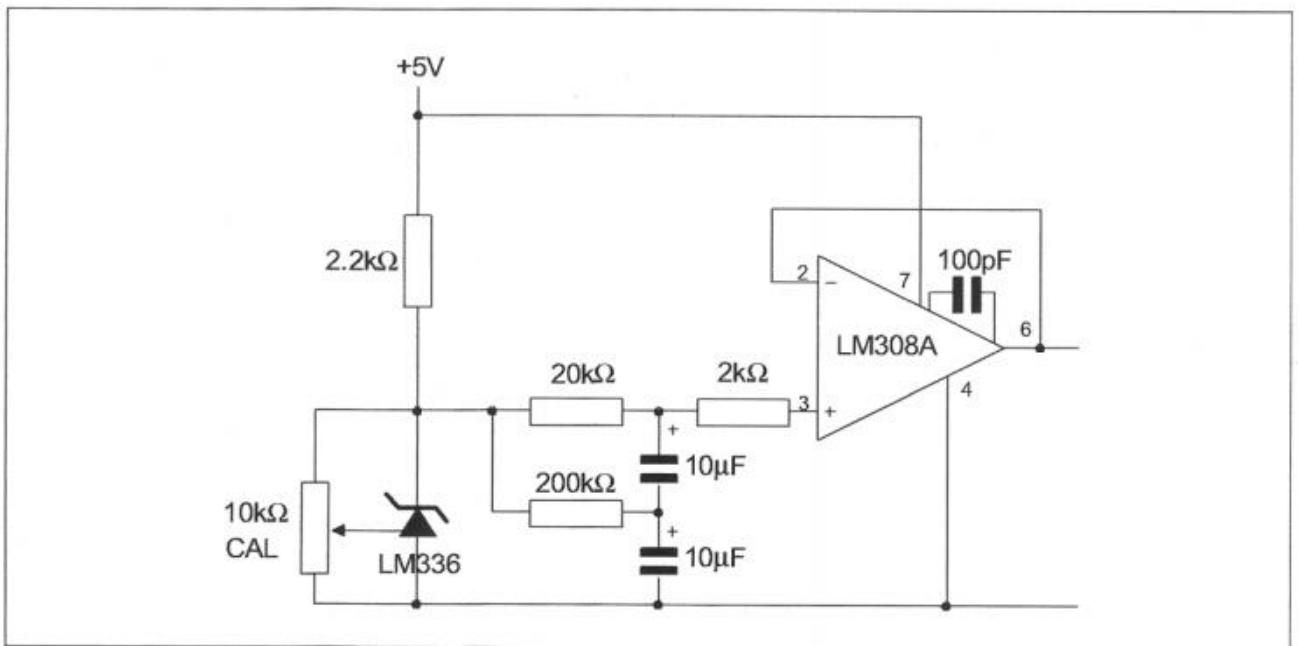
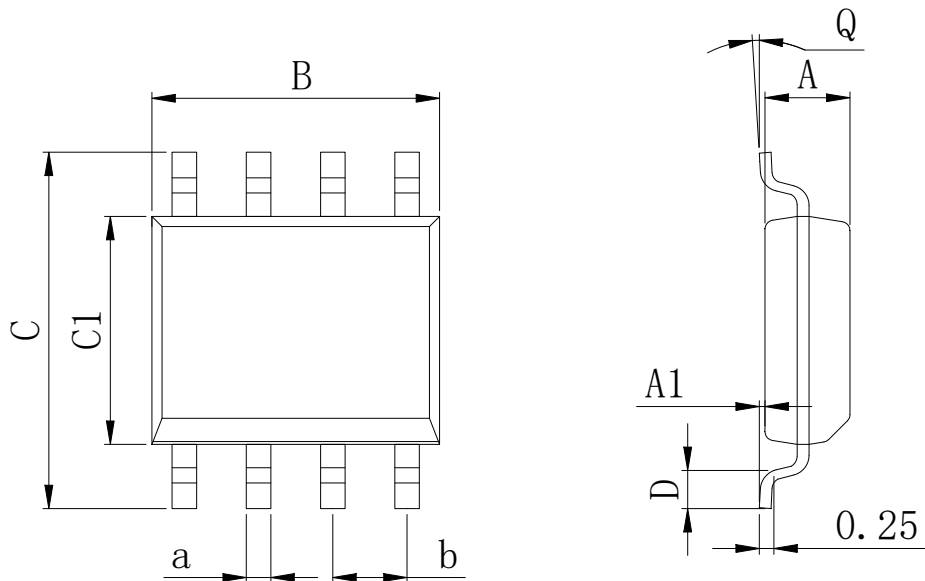


Figure 10 : Low Noise Buffered Reference



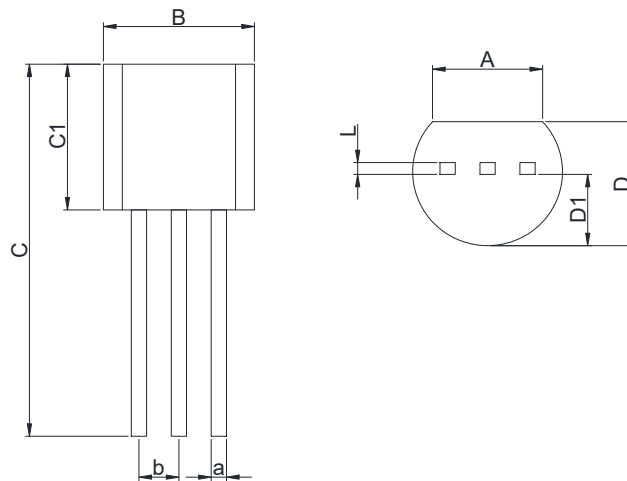
**Physical Dimensions**

SOP-8


**Dimensions In Millimeters(SOP-8)**

Symbol:	A	A1	B	C	C1	D	Q	a	b
Min:	1.35	0.05	4.90	5.80	3.80	0.40	0°	0.35	1.27 BSC
Max:	1.55	0.20	5.10	6.20	4.00	0.80	8°	0.45	

TO-92

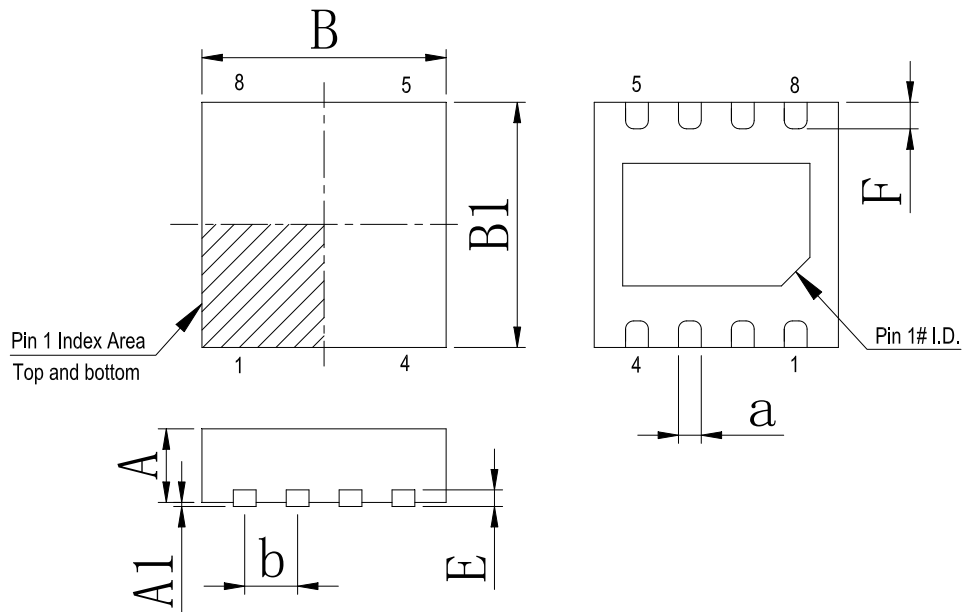

**Dimensions In Millimeters(TO-92)**

Symbol:	A	B	C	C1	D	D1	L	a	b
Min:	3.43	4.44	11.2	4.32	3.17	2.03	0.33	0.40	1.27BSC
Max:	3.83	5.21	12.7	5.34	4.19	2.67	0.42	0.52	



## Physical Dimensions

DFN-8 3\*3



Dimensions In Millimeters(DFN-8 3*3)								
Symbol:	A	A1	B	B1	E	F	a	b
Min:	0.85	0.00	2.90	2.90	0.20	0.30	0.20	0.65 BSC
Max:	0.95	0.05	3.10	3.10	0.25	0.50	0.34	

## Revision History

DATE	REVISION	PAGE
2018-9-5	New	1-11
2023-9-13	Update Lead Temperature、 Add annotation for Maximum Ratings.	2

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